

L Number	Hits	Search Text	DB	Time stamp
1	5	618431.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 12:09
2	2	("5832008").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 12:10
3	2	("4833333").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 12:34
4	0	("pulseadj (widthduration) and pulseadj (repetition frequency) and Q adj switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 12:35
5	646	pulse adj (width duration) and pulse adj (repetition frequency frequencies) and Q adj switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 12:35
6	8	(variable varies vary tune tuning tunable adjust adjustable) near4 pulse adj (width duration) and (varies vary variable tunable tune tuning adjust adjustable) near4 pulse adj (repetition frequency frequencies) and Q adj switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 12:46
7	2	(variable varies vary tune tuning tunable adjust adjustable) near4 pulse adj (width duration) and (varies vary variable tunable tune tuning adjust adjustable) near4 pulse adj (repetition frequency frequencies) and Q adj switch\$3.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 12:43
8	175	(Q-switch\$3 Q adj switch\$3).ti,ab,clm. and laser.ti,ab,clm. and passive.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 12:47
10	0	(Q-switch\$3 Q adj switch\$3).ti,ab,clm. and laser.ti,ab,clm. and passive.ti,ab,clm. and pulse adj (duration width) near4 (adjustable adjust adjusting variable tunable tuning varying varies tune) and pulse adj (frequency repetition interval) near4 (adjustable adjust adjusting variable tunable tuning varying varies tune)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 12:48
9	6	(Q-switch\$3 Q adj switch\$3).ti,ab,clm. and laser.ti,ab,clm. and passive.ti,ab,clm. and pulse adj (duration width) near4 (adjustable adjust adjusting variable tunable tuning varying varies tune)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 13:08
11	44	(Q-switch\$3 Q adj switch\$3).ti,ab,clm. and laser.ti,ab,clm. and pulse adj (duration width) near4 (adjustable adjust adjusting variable tunable tuning varying varies tune)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 13:11
12	10	(Q-switch\$3 Q adj switch\$3).ti,ab,clm. and laser.ti,ab,clm. and pulse adj (duration width) near4 (adjustable adjust adjusting variable tunable tuning varying varies tune) and repetition adj (frequencies frequency interval intervals)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 13:14

13	7	(Q-switch\$3 Q adj switch\$3).ti,ab,clm. and laser.ti,ab,clm. and pulse adj (duration width) near4 (adjustable adjust adjusting variable tunable tuning varying varies tune) and repetition adj (frequencies frequency interval intervals) and (coat coating coated)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 13:16
14	0	(Q-switch\$3 Q adj switch\$3).ti,ab,clm. and laser.ti,ab,clm. and pulse adj (duration width) near4 (adjustable adjust adjusting variable tunable tuning varying varies tune) and repetition adj (frequencies frequency interval intervals) and (coat coating coated) near4 (variable ramp ramped inclined inclination)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 13:16
15	0	(Q-switch\$3 Q adj switch\$3).ti,ab,clm. and laser.ti,ab,clm. and pulse adj (duration width) near4 (adjustable adjust adjusting variable tunable tuning varying varies tune) and repetition adj (frequencies frequency interval intervals) and (coat coating coated) near4 (tune tuning)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 13:17
16	7	(Q-switch\$3 Q adj switch\$3).ti,ab,clm. and laser.ti,ab,clm. and pulse adj (duration width) near4 (adjustable adjust adjusting variable tunable tuning varying varies tune) and repetition adj (frequencies frequency interval intervals) and (coat coating coated)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 13:26
17	7	(Q-switch\$3 Q adj switch\$3).ti,ab,clm. and laser.ti,ab,clm. and pulse adj (duration width) near4 (adjustable adjust adjusting variable tunable tuning varying varies tune) and (repetition adj (frequencies frequency interval intervals) pulse adj spacing) and (coat coating coated)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 13:26
18	9	(Q-switch\$3 Q adj switch\$3).ti,ab,clm. and laser.ti,ab,clm. and pulse adj (duration width) near4 (adjustable adjust adjusting variable tunable tuning varying varies tune) and (repetition adj (frequencies frequency interval intervals) pulse adj (repetition adj rate spacing)) and (coat coating coated)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 13:43
19	2	("5331651").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 13:43
20	2	("5329544").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 13:44
21	2	("5249196").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 13:45
22	0	("(Qadjswitch\$3Q-switchingQ-switch).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 13:46
23	2924	(Q adj switch\$3 Q-switch\$3).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 13:46

24	9	(Q adj switch\$3 Q-switch\$3).ti,ab,clm. and tunable near6 (repetition pulse adj rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 13:47
25	0	(Q adj switch\$3 Q-switch\$3).ti,ab,clm. and tunable near6 (repetition pulse adj rate) and tunable near6 (width duration length time)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 13:48
26	2	(Q adj switch\$3 Q-switch\$3).ti,ab,clm. and tunable near6 (repetition pulse adj rate) and tunable near6 (width duration length time)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 13:48
27	1	(Q adj switch\$3 Q-switch\$3).ti,ab,clm. and tunable near6 (repetition pulse adj rate) and tunable near6 (width duration length time) and coat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 14:18
28	0	(Q adj switch\$3 Q-switch\$3).ti,ab,clm. and tunable near6 (repetition pulse adj rate) and tunable near6 (width duration length time) and coat\$3 and (372/4\$1.ccls. 372/50.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 14:19
29	1	(Q adj switch\$3 Q-switch\$3).ti,ab,clm. and tunable near6 (repetition pulse adj rate) and tunable near6 (width duration length time) and coat\$3 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 14:19
30	7	(((372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50) or (372/75) or (372/10) or (372/11) or (372/12) or (372/13) or (372/14) or (372/15) or (372/16)).CCLS.) and (algaas inp gallium adj alumin\$lum adj arsenide alumin\$lum adj gallium adj arsenide indium adj phosphide) and passive adj (Q-switch Q-switching)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 15:29
31	69	(((372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50) or (372/75) or (372/10) or (372/11) or (372/12) or (372/13) or (372/14) or (372/15) or (372/16)).CCLS.) and (Q-switch Q-switching).ti,ab,clm. and (varying varies vary variable tuning tune tunes tunable adjusts adjust adjusting adjustable) near6 pulse	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 16:02
32	1364	(372/20).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 16:03
33	108	((372/20).CCLS.) and (Q-switch Q adj switch Q-switching Q switching).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 16:04
34	19	((372/20).CCLS.) and (Q-switch Q adj switch Q-switching Q switching).ti,ab,clm. and repetition and pulse adj (duration length width)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 16:05
35	4	((372/20).CCLS.) and (Q-switch Q adj switch Q-switching Q switching).ti,ab,clm. and (variable tunable adjustable varying tuning adjusting) near4 (repetition pulse adj (duration length width))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 16:10

36	35	372/25.ccls. and (Q-switch Q adj switch Q-switching Q switching).ti,ab,clm. and (variable tunable adjustable varying tuning adjusting) near4 (repetition pulse adj (duration length width))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 16:11
37	8	372/25.ccls. and (Q-switch Q adj switch Q-switching Q switching).ti,ab,clm. and (variable tunable adjustable varying tuning adjusting) near4 (repetition pulse adj (duration length width)) and coating	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 16:21
38	0	372/25.ccls. and (Q-switch Q adj switch Q-switching Q switching).ti,ab,clm. and (variable tunable adjustable varying tuning adjusting) near4 (repetition pulse adj (duration length width)) and coating near3 (graded grading)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 16:13
39	132	372/25.ccls. and (Q-switch Q adj switch Q-switching Q switching).ti,ab,clm. and (variable tunable adjustable varying tuning adjusting)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 16:27
40	0	372/25.ccls. and graded adj coating	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 16:24
41	0	372/25.ccls. and (grading graded) near4 (coating thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 16:25
42	2142	(Q-switch Q adj switch Q-switching Q switching).ti,ab,clm. and (variable tunable adjustable varying tuning adjusting) and 257/\$9.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 16:28
43	390	(Q-switch Q adj switch Q-switching Q switching).ti,ab,clm. and (variable tunable adjustable varying tuning adjusting) and coating and 257/\$9.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 16:30
44	159	(Q-switch Q adj switch Q-switching Q switching).ti,ab,clm. and (variable tunable adjustable varying tuning adjusting) and coating and laser and 257/\$9.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 16:31
-	243	q-switch.ti. and laser.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 19:49
-	215	q-switch.ti. and laser.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 10:17
-	2	q-switch.ti. and laser.ti. and (fabry-perot or f-p).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 11:05
-	31	passive adj (q-switch or q-switching) and semiconductor and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 11:15
-	6	passive adj (q-switch or q-switching).ti,ab. and semiconductor and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 11:16

-	3	passive adj (q-switch or q-switching).ti,ab. and semiconductor.ti,ab. and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 11:16
-	17	(US-6351478-\$ or US-6340806-\$ or US-6335942-\$ or US-3660777-\$ or US-6400495-\$ or US-5274650-\$ or US-5408480-\$ or US-5461637-\$ or US-5005176-\$ or US-5541948-\$).did. or (US-3660777-\$ or US-5541948-\$).did. or (US-6172997-\$ or US-6259711-\$ or US-6263004-\$ or US-6240113-\$ or US-6061378-\$).did.	USPAT; EPO; DERWENT	2002/07/13 11:17
-	0	(US-6351478-\$ or US-6340806-\$ or US-6335942-\$ or US-3660777-\$ or US-6400495-\$ or US-5274650-\$ or US-5408480-\$ or US-5461637-\$ or US-5005176-\$ or US-5541948-\$).did. or (US-3660777-\$ or US-5541948-\$).did. or (US-6172997-\$ or US-6259711-\$ or US-6263004-\$ or US-6240113-\$ or US-6061378-\$).did.	USPAT; EPO; DERWENT	2002/07/13 11:18
-	284	(372/10).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 13:18
-	157	(372/11).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 13:18
-	5180	(372/43).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:29
-	4	((372/11).CCLS.) and ((372/43).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 13:43
-	178	(passive or passively) near3 (q-switch or q-switching)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 13:19
-	0	((372/11).CCLS.) and ((372/43).CCLS.)) and ((passive or passively) near3 (q-switch or q-switching))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 13:19
-	95	semiconductor.ti,ab. and laser.ti,ab. and (q-switch or q-switching or passive\$2 near3 switch\$3) and 372/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 13:44
-	22	semiconductor.ti,ab. and laser.ti,ab. and (q-switch or q-switching or passive\$2 near3 switch\$3).ti,ab. and 372/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 15:36
-	5	semiconductor.ti,ab. and laser.ti,ab. and (q-switch or q-switching or passive\$2 near3 switch\$3).ti,ab. and 372/\$6.ccls. and passive	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 15:45

-	11	laser.ti,ab. and (q-switch or q-switching or passive\$2 near3 switch\$3).ti,ab. and 372/\$6.ccls. and (variable or vary) near4 wavelength	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 15:48
-	1	semiconductor adj laser and (passively or passive) adj (q-switch or q-switching) and (variable or vary or varies) near3 (wavelength or frequency or frequencies)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 16:02
-	157	(372/11).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 16:02
-	43	((372/11).CCLS.) and semiconductor near3 (laser or q-switch)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 16:03
-	0	((372/11).CCLS.) and semiconductor near3 (laser or q-switch)) and q-switch near4 (tune or variable) near4 (wavelength or frequency)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 16:04
-	0	((372/11).CCLS.) and semiconductor near3 (laser or q-switch)) and q-switch near12 (tune or variable) near12 (wavelength or frequency)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 16:04
-	15	((372/11).CCLS.) and semiconductor near3 (laser or q-switch)) and ((tune or tuning) near12 (wavelength or frequency))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 16:04
-	5578	((372/10).CCLS.) or ((372/11).CCLS.) or ((372/43).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:30
-	0	((372/10).CCLS.) or ((372/11).CCLS.) or ((372/43).CCLS.) and (coated or coating) near12 (reflector or reflecting or reflect) near12 thickness near12 (infrared or infra-red or IR) and (Q-switch or Q-switching) near12 (passive or passively)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:33
-	0	((372/10).CCLS.) or ((372/11).CCLS.) or ((372/43).CCLS.) and (coated or coating or coat) near12 (reflector or reflecting or reflect) near12 (thick or thickness) and (Q-switch or Q-switching) near12 (passive or passively)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:34
-	0	((372/10).CCLS.) or ((372/11).CCLS.) or ((372/43).CCLS.) and (layer or film or cover or covering or coated or coating or coat) near12 (reflector or reflecting or reflect) near12 (thick or thickness) and (Q-switch or Q-switching) near12 (passive or passively)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:35
-	0	(layer or film or cover or covering or coated or coating or coat) near12 (reflector or reflecting or reflect) near12 (thick or thickness) and (Q-switch or Q-switching) near12 (passive or passively)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:35
-	27	(layer or film or cover or covering or coated or coating or coat) near12 (thick or thickness) and (Q-switch or Q-switching) near12 (passive or passively)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:36

-	14	(layer or film or cover or covering or coated or coating or coat) near12 (thick or thickness) and (Q-switch or Q-switching) near12 (passive or passively) and semiconductor near12 laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 18:13
-	18	(layer or film or cover or covering or coated or coating or coat) near12 (thick or thickness) and Q-switch\$3 near12 (passive or passively) and semiconductor near12 laser	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 18:13
-	4	((layer or film or cover or covering or coated or coating or coat) near12 (thick or thickness) and Q-switch\$3 near12 (passive or passively) and semiconductor near12 laser) not ((layer or film or cover or covering or coated or coating or coat) near12 (thick or thickness) and (Q-switch or Q-switching) near12 (passive or passively) and semiconductor near12 laser)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 18:27
-	1	ar adj coating near12 (gradient or variable or graded or non-uniform or nonuniform) and q-switch\$3 near12 semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 18:33
-	1	coating near12 (gradient or variable or graded or non-uniform or nonuniform) and passive\$2 near12 q-switch\$3 and semiconductor	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 18:35
-	1	graded near12 coating and passive\$2 near12 q-switch\$3 and semiconductor	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 18:36
-	1	graded near12 coat\$3 and passive\$2 near12 q-switch\$3 and semiconductor	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 18:36
-	5	ar near12 coat\$3 and passive\$2 near12 q-switch\$3 and semiconductor	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 18:53
-	2	("6215805").PN.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 19:11
-	0	("modulat\$3 near12 (thickness or coat\$3) near12 q-switch\$3").PN.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 19:11
-	3	modulat\$3 near12 (thickness or coat\$3) near12 q-switch\$3	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 19:15
-	1	modulat\$3 near12 (ar or anti-reflective or antireflective) near12 q-switch\$3	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 19:15
-	6749	((372/10) or (372/11) or (372/14) or (372/15) or (372/16) or (372/43) or (372/75)).CCLS.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 11:04

-	19	(((372/10) or (372/11) or (372/14) or (372/15) or (372/16) or (372/43) or (372/75)).CCLS.) and passive\$2 near10 q-switch\$3 and semiconductor and coat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 13:39
-	0	(((372/10) or (372/11) or (372/14) or (372/15) or (372/16) or (372/43) or (372/75)).CCLS.) and graded adj2 ar adj coatings near4 thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 13:40
-	0	(((372/10) or (372/11) or (372/14) or (372/15) or (372/16) or (372/43) or (372/75)).CCLS.) and graded near4 ar adj coatings near4 thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 13:40
-	0	(((372/10) or (372/11) or (372/14) or (372/15) or (372/16) or (372/43) or (372/75)).CCLS.) and graded near4 coatings near4 thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 13:41
-	1	graded near4 (antireflective or ar) adj2 coatings, near4 thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 13:42
-	1	graded near4 (antireflective or ar) adj2 coatings near4 (thick or thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 13:43
-	6585	graded adj index (antireflective or ar) adj2 coating	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 13:43
-	1	graded adj index adj (antireflective or ar) adj coating	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 14:31
-	6	graded near9 (antireflective or ar) adj coating same thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 15:10
-	2	("6215805").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 15:14
-	0	("66160824").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 15:15
-	2	("6160824").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 15:16
-	1	((tune or tuning) near12 q-switch\$3) near12 (translat\$3 or rotat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 15:46
-	0	rotation-induced near12 (tune or tuning) near12 q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 15:47

-	0	translation-induced near12 (tune or tuning) near12 q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 15:47
-	0	translation-induced near12 (tune or tuning) and q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 15:47
-	0	rotation-induced near12 (tune or tuning) and q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 15:47
-	87	rotat\$3 near12 (tune or tuning) and q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 15:48
-	43	(rotate or rotation) near12 (tune or tuning) and q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 15:48
-	7	(rotate or rotation) near12 (tune or tuning) and q-switch\$3 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 16:25
-	0	(rotate or rotation) near12 (tune or tuning) and passive\$2 near3 q-switch\$3 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 15:49
-	4	713436.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 16:30
-	4	semiconductor near2 passive\$2 near3 q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 17:15
-	7	(infrared or ir) adj absorption near6 gaas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 17:43
-	4	(mqw or (multiple-quantum-well or multiple adj quantum adj well)) near3 q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 18:24
-	0	(inp or algaas or indium adj phosphide or aluminum adj gallium adj arsenide) near12 q-switch\$3 near12 passive\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 18:26
-	5	(inp or algaas or indium adj phosphide or aluminum adj gallium adj arsenide) near12 q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 20:42
-	0	(inp or algaas or indium adj phosphide or aluminum adj gallium adj arsenide) near12 q-switch\$3 and passive\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 18:26

-	3	("5015353").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 20:43
-	3	("4868834").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 20:43
-	2	("6215805").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:33
-	12594	((372/10) or (372/11) or (372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:36
-	412	372/12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:36
-	244	372/13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:36
-	244	372/13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:37
-	110	372/14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:37
-	143	372/15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:37
-	112	372/16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:37
-	13339	((((372/10) or (372/11) or (372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50)).CCLS.) or 372/12 or 372/13 or 372/13 or 372/14 or 372/15 or 372/16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:37
-	60	((((372/10) or (372/11) or (372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50)).CCLS.) or 372/12 or 372/13 or 372/13 or 372/14 or 372/15 or 372/16) and (passive or passively) near3 (Q adj switch or Q-switch)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:38
-	28	(((((372/10) or (372/11) or (372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50)).CCLS.) or 372/12 or 372/13 or 372/13 or 372/14 or 372/15 or 372/16) and (passive or passively) near3 (Q adj switch or Q-switch)) and (rotat\$3 or translat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:57

-	7	(((((372/10) or (372/11) or (372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50)).CCLS.) or 372/12 or 372/13 or 372/13 or 372/14 or 372/15 or 372/16) and (passive or passively) near3 (Q adj switch or Q-switch)) and (rotat\$3 or translat\$3) near12 axis	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 18:42
-	4	618431.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 18:52
-	0	rotat\$3 near12 (Q-switch or Q adj switch) near12 tun\$3	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 18:53
-	3	rotat\$3 near12 (Q-switch or Q adj switch) and tun\$3 and 372/4\$1.ccls.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 18:57
-	10	(rotate or rotating) near12 (Q-switch or Q adj switch) and (tune or tuning) and (372/4\$1.ccls. or 372/1\$1.ccls.)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 19:22
-	1186	(372/75).CCLS.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 19:22
-	8	((372/75).CCLS.) and (Q-switch or Q adj switch) near6 (passive or passively)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 19:24
-	0	((372/75).CCLS.) and (Q-switch or Q adj switch) near6 (passive or passively) same (moving or move or translate or translation or rotate or rotation)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 19:24
-	4	618431.ap.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 08:42
-	33	(US-6340806-\$ or US-6400495-\$ or US-6351478-\$ or US-5005176-\$ or US-5274650-\$ or US-5832008-\$ or US-5408480-\$ or US-6292504-\$ or US-6252892-\$ or US-6026101-\$ or US-6373864-\$ or US-6373865-\$ or US-3660777-\$ or US-5023878-\$ or US-5257274-\$ or US-6335942-\$ or US-6330259-\$ or US-5541948-\$ or US-5414724-\$ or US-5461637-\$ or US-6215805-\$ or US-6160824-\$ or US-5015353-\$ or US-4868834-\$).did. or (US-20020141457-\$ or US-20030007520-\$ or US-20030031215-\$ or US-20020051470-\$).did. or (US-3660777-\$ or US-5541948-\$).did. or (US-6240113-\$ or US-6172997-\$ or US-6061378-\$ or US-6263004-\$ or US-6259711-\$).did.	USPÄT; US-PGPUB; EPO; DERWENT	2003/09/28 10:27
-	0	tunable near3 (Q adj switch Q-switch Q-switching Q adj switching) near12 (varying variable adjusting adjustment selection selecting setting) near12 thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 10:30

-	0	tunable near3 (Q adj switch Q-switch Q-switching Q adj switching) near12 thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 10:31
-	0	(tuning tune tunable) near3 (Q adj switch Q-switch Q-switching Q adj switching) near12 thickness	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 10:31
-	0	(tuning tune tunable) near3 (Q adj switch Q-switch Q-switching Q adj switching) near12 (thickness optical adj path)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 10:32
-	1595	(Q-switch Q adj switch).ti,ab,clm.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 10:32
-	315	(Q-switch Q adj switch).ti,ab,clm. and (thickness optical adj path path adj length)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 10:32
-	62	(Q-switch Q adj switch).ti,ab,clm. and (thickness optical adj path path adj length) and (tune tuning tunable)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 10:43
-	33	(Q-switch Q-switching Q adj switch Q adj switching) near6 lens.ti,ab,clm.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 11:29
-	2	semiconductor.ti,ab,clm. and (Q-switch Q-switching Q adj switch Q adj switching) near6 lens.ti,ab,clm.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 11:30
-	3	(257/\$9.ccls. 372/4\$1.ccls. 372/50.ccls. semiconductor.ti,ab,clm.) and (Q-switch Q-switching Q adj switch Q adj switching) near6 lens.ti,ab,clm.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 11:56
-	156	(Q-switch Q-switching Q adj switching Q adj switch).ti,ab,clm. and saturable adj absorb\$3	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 11:57
-	46	(passive near2 (Q-switch Q-switching Q adj switching Q adj switch)).ti,ab,clm. and saturable adj absorb\$3	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 11:59
-	5	(passive near2 (Q-switch Q-switching Q adj switching Q adj switch)).ti,ab,clm. and saturable adj absorb\$3 and (graded gradient variable near3 thickness)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 12:00
-	5	(passive near2 (Q-switch Q-switching Q adj switching Q adj switch)).ti,ab,clm. and saturable adj absorb\$3 and (graded gradient variable near3 thickness) and passive	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 12:40
-	3	("4519082" "4644550" "4672619").PN.	USPÄT	2003/09/28 12:24
-	2	4833333.URPN.	USPAT	2003/09/28 12:24
-	2	("6180824").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 12:41

-	2	("6160824").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 13:02
-	2	("4833333").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 13:05
-	2	("5802083").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 13:05
-	0	("semiconductorand((Qadj (switchswitching)) Q-switch Q-switching) near3 (passive passively))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 13:05
-	61	semiconductor and ((Q adj (switch switching)) Q-switch Q-switching) near3 (passive passively)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 19:51
-	21	semiconductor and ((Q adj (switch switching)) Q-switch Q-switching) near3 (passive passively) and ((variable varying varies vary) near2 thickness graded grading grade gradient)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 20:15
-	47	semiconductor and ((Q adj (switch switching)) Q-switch Q-switching) near3 (passive passively) and ((variable varying varies vary) near2 thickness graded grading grade gradient transmittance coating coated)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 20:20
-	26	(semiconductor and ((Q adj (switch switching)) Q-switch Q-switching) near3 (passive passively) and ((variable varying varies vary) near2 thickness graded grading grade gradient transmittance coating coated)) not (semiconductor and ((Q adj (switch switching)) Q-switch Q-switching) near3 (passive passively) and ((variable varying varies vary) near2 thickness graded grading grade gradient))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 20:16
-	43	semiconductor and ((Q adj (switch switching)) Q-switch Q-switching) near3 (passive passively) and ((variable varying varies vary graded grading gradient) near2 thickness transmittance coating coated)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 20:21
-	26	(semiconductor and ((Q adj (switch switching)) Q-switch Q-switching) near3 (passive passively) and ((variable varying varies vary graded grading gradient) near2 thickness transmittance coating coated)) not (semiconductor and ((Q adj (switch switching)) Q-switch Q-switching) near3 (passive passively) and ((variable varying varies vary) near2 thickness graded grading grade gradient))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 21:07
-	21	(lithium adj fluoride lif) near6 semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 21:11
-	2	laser and host adj material near6 ("ho.sup.3+" holmium) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 21:10

-	13	(lithium adj fluoride lif) near3 semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 21:24
-	2	ylf adj laser.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 21:26
-	0	semiconductor adj passive adj Q-switch and lens	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 21:26
-	0	semiconductor adj passive adj Q-switch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 21:26
-	19	(coating coated) near6 Q-switch and passive adj2 Q-switch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 10:12
-	0	(coating coated) near6 Q-switch and passive adj2 Q-switch near6 semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 10:12
-	2	(coating coated) near6 Q-switch and passive adj2 Q-switch and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 10:20
-	2	(coating coated) near12 Q-switch and passive adj2 Q-switch and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 10:24
-	0	(coating coated) near12 saturable adj absorber and passive adj2 Q-switch and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:10
-	6	(optical optically) near6 (polish polishing polished) and passive adj Q-switch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:13
-	0	(polish polishing polished) near12 passive adj Q-switch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:14
-	32	(polish polishing polished) and passive adj Q-switch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:14
-	4	(polish polishing polished) and passive adj Q-switch.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:20
-	3989	(polish polishing polished) near6 lens	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:20

-	1	(polish polishing polished) near6 lens and laser and Q-switch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:23
-	1870	(polish polishing polished) near6 lens.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:23
-	542	(polish polishing polished) near6 lens.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:23
-	0	(polish polishing polished) near6 lens near6 reflection.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:23
-	11	(polish polishing polished) near6 lens near6 reduce.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:47
-	1870	(polish polishing polished) near6 lens.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:47
-	533	(optical optically) near12 (polish polishing polished) near6 lens.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:47
-	471	(optical optically) near12 (polish polishing polished) near6 lens.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:49
-	361	(optical optically) near6 (polish polishing polished) near6 lens.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:49
-	188	(optical optically) near3 (polish polishing polished) near3 lens.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:51
-	74	(optical optically) near1 (polish polishing polished) near3 lens.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 12:31
-	8	(optical optically) near1 (polish polishing polished) and Q-switch.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 12:44
-	59	output adj (coupler coupling) near8 Q-switch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 13:04
-	22	(mqw multiple adj quantum adj well) and q-switch and laser.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 13:07

-	3	(mqw multiple adj quantum adj well).ti,ab,clm. and q-switch and laser.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 13:09
-	1570	(mqw multiple adj quantum adj well).ti,ab,clm. and laser.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 13:09
-	227	(mqw multiple adj quantum adj well).ti. and laser.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 13:09
-	192	(mqw multiple adj quantum adj well).ti. and laser.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 13:11
-	12	(mqw multiple adj quantum adj well) near6 advantage and laser.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 13:36
-	2	("5832008").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 13:53
-	0	("passiveadjQ-switchnear12(inpindiumadjphosphideidegaasalalgaasgaalasgalliumadjalumin?umadjarsenide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 13:54
-	0	passive adj Q-switch near15 (inp indium phosphide ide gaasal algaas gaalas gallium adj alumin?um adj arsenide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 13:55
-	0	passive adj Q-switch near15 (inp indium phosphide ide gaasal algaas gaalas gallium adj alumin\$um adj arsenide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 14:16
-	14493	((372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50) or (372/75) or (372/10) or (372/11) or (372/12) or (372/13) or (372/14) or (372/15) or (372/16)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 14:18
-	7	((372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50) or (372/75) or (372/10) or (372/11) or (372/12) or (372/13) or (372/14) or (372/15) or (372/16)).CCLS.) and (algaas inp gallium adj alumin\$lum adj arsenide alumin\$lum adj gallium adj arsenide indium adj phosphide) and passive adj (Q-switch Q-switching)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 15:29
-	2	914404.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 16:46